Renesas Electronics America Inc - R5F117GCGFB#30 Datasheet

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

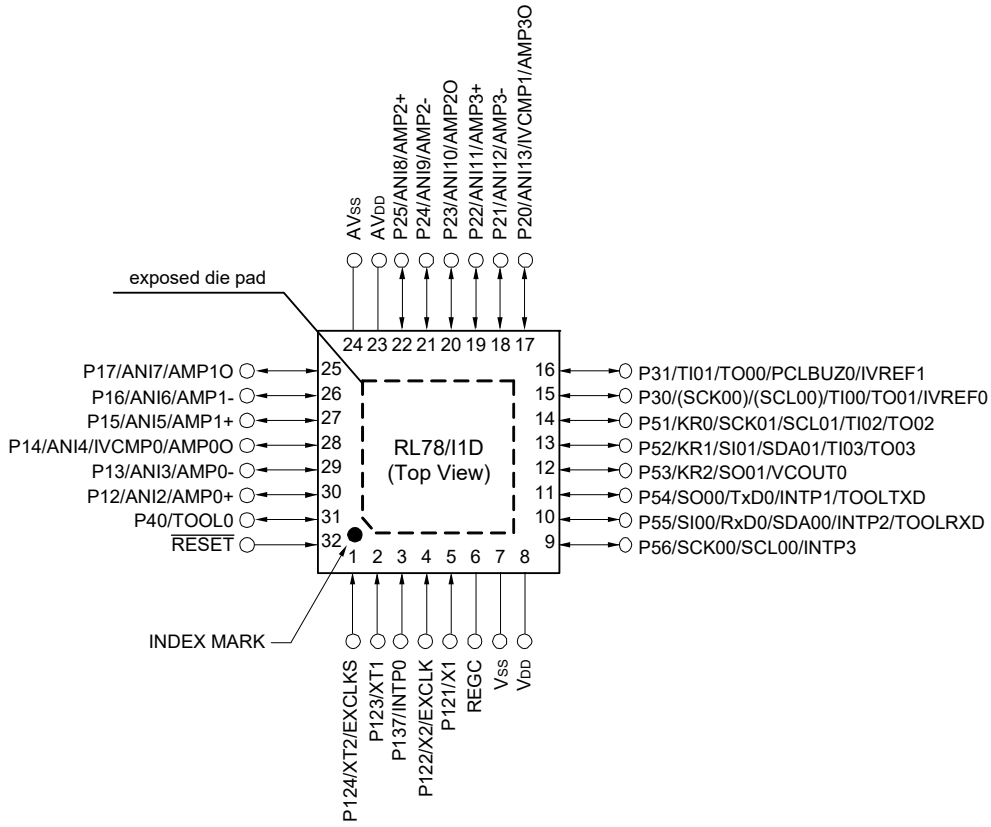
Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, WDT
Number of I/O	33
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 17x8/12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f117gcgfb-30

Pin count	Package	Ordering Part Number
20 pins	20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)	R5F11768GSP#30, R5F1176AGSP#30, R5F11768GSP#50, R5F1176AGSP#50
24 pins	24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)	R5F11778GNA#U0, R5F1177AGNA#U0, R5F11778GNA#W0, R5F1177AGNA#W0
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	R5F117A8GSP#30, R5F117AAGSP#30, R5F117ACGSP#30, R5F117A8GSP#50, R5F117AAGSP#50, R5F117ACGSP#50
32 pins	32-pin plastic HVQFN (5 × 5 mm, 0.5 mm pitch)	R5F117BAGNA#20, R5F117BCGNA#20, R5F117BAGNA#40, R5F117BCGNA#40
	32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)	R5F117BAGFP#30, R5F117BCGFP#30, R5F117BAGFP#50, R5F117BCGFP#50
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	R5F117GAGFB#30, R5F117GCGFB#30, R5F117GAGFB#50, R5F117GCGFB#50

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.4 32-pin products

<R> • 32-pin plastic HVQFN (5 × 5 mm, 0.5 mm pitch)



Caution 1. Connect the REGC pin to VSS pin via a capacitor (0.47 to 1 μF).

Caution 2. Make AVSS pin the same potential as VSS pin.

Caution 3. Make AVDD pin the same potential as VDD pin.

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 (PIOR0).

Remark 3. It is recommended to connect an exposed die pad to VSS.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X) Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 3.6 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	
		1.8 V ≤ V_{DD} < 2.4 V	1.0		8.0	
		1.6 V ≤ V_{DD} < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (f_{XT}) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **6.4 System Clock Oscillator** in the RL78/I1D User's Manual.

2.2.2 On-chip oscillator characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{IH}			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to +85°C	1.8 V ≤ V_{DD} ≤ 3.6 V	-1.0		+1.0	%
			1.6 V ≤ V_{DD} < 1.8 V	-5.0		+5.0	
		-40 to -20°C	1.8 V ≤ V_{DD} ≤ 3.6 V	-1.5		+1.5	%
			1.6 V ≤ V_{DD} < 1.8 V	-5.5		+5.5	
		+85 to +105°C	2.4 V ≤ V_{DD} ≤ 3.6 V	-2.0		+2.0	%
Middle-speed on-chip oscillator oscillation frequency Note 2	f_{IM}			1		4	MHz
Middle-speed on-chip oscillator oscillation frequency accuracy		1.8V ≤ V_{DD} ≤ 3.6V		-12		+12	%
Low-speed on-chip oscillator clock frequency Note 2	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(4/5)**

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Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P04, P30 to P33, P40, P50 to P57, P130	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -2.0 mA	V_{DD} - 0.6			V
			1.8 V ≤ V_{DD} ≤ 3.6 V Note 3, I_{OH} = -1.5 mA	V_{DD} - 0.5			V
			1.6 V ≤ V_{DD} ≤ 3.6 V Note 1, I_{OH} = -1.0 mA	V_{DD} - 0.5			V
	V_{OH2}	P10 to P17, P20 to P25	1.6 V ≤ AV_{DD} ≤ 3.6 V Note 2, I_{OH} = -100 μA	AV_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00 to P04, P30 to P33, P40, P50 to P57, P130	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 3.0 mA			0.6	V
			2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 1.5 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 3.6 V Note 3, I_{OL} = 0.6 mA			0.4	V
			1.6 V ≤ AV_{DD} ≤ 3.6 V Note 1, I_{OL} = 0.3 mA			0.4	V
	V_{OL2}	P10 to P17, P20 to P25	1.6 V ≤ AV_{DD} ≤ 3.6 V Note 2, I_{OL} = 400 μA			0.4	V
	V_{OL3}	P60 to P63	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 3.0 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 3.6 V Note 3, I_{OL} = 2.0 mA			0.4	V
			1.6 V ≤ AV_{DD} ≤ 3.6 V Note 1, I_{OL} = 1.0 mA			0.4	V

Note 1. Only T_A = -40 to +85°C is guaranteed.

Note 2. The condition that 2.4 V ≤ AV_{DD} ≤ 3.6 V is guaranteed when +85°C < T_A ≤ +105°C.

Note 3. The condition that 2.4 V ≤ V_{DD} ≤ 3.6 V is guaranteed when +85°C < T_A ≤ +105°C.

Caution P30 and P51 to P56 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

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Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The MAX values include the peripheral operating current. However, these values do not include the current flowing into the A/D converter, operational amplifier, comparator, LVD circuit, I/O ports, and on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.

Note 2. When the HALT instruction is executed in the flash memory.

Note 3. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 4. When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 5. When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and high-speed on-chip oscillator clock are stopped. When RTCLPC = 1 and ultra-low-power consumption oscillation is set (AMPHS1, AMPHS0) = (1, 0). The values include the current flowing into the real-time clock. However, the values do not include the current flowing into the 12-bit interval timer and watchdog timer.

Note 6. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, high-speed system clock, and sub clock are stopped.

Note 7. When the high-speed system clock, high-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)

Remark 3. f_{IM}: Middle-speed on-chip oscillator clock frequency (4 MHz max.)

Remark 4. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 5. f_{SX}: Sub clock frequency (XT1 clock oscillation frequency)

Remark 6. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency or low-speed on-chip oscillator clock frequency)

Remark 7. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(4/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD3} Note 2	STOP mode Note 3	T_A = -40°C		0.16	0.51	μA
			T_A = +25°C		0.22	0.51	
			T_A = +50°C		0.27	1.10	
			T_A = +70°C		0.37	1.90	
			T_A = +85°C		0.60	3.30	
			T_A = +105°C		1.50	17.00	

<R> **Note 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The MAX values include the peripheral operating current. However, these values do not include the current flowing into the A/D converter, operational amplifier, comparator, LVD circuit, I/O ports, and on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.

Note 2. The values do not include the current flowing into the real-time clock, 12-bit interval timer, and watchdog timer.

Note 3. For the setting of the current values when operating the subsystem clock in STOP mode, see the current values when operating the subsystem clock in HALT mode.

Note 1. Current flowing to V_{DD}.

Note 2. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and high-speed system clock are stopped.

<R> **Note 3.** Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.

Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.

Note 8. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{CMP} when the comparator circuit is in operation.

Note 9. Current flowing only to the 8-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 8-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

Note 10. Current flowing to AV_{DD}.

Note 11. Current flowing into AV_{REFP}.

Note 12. Current consumed by generating the internal reference voltage (1.45 V).

Note 13. Current flowing only to the operational amplifier. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{AMP} when the operational amplifier is operating in operating mode, HALT mode, or STOP mode.

Note 14. The values include the operating current of the operational amplifier reference current circuit.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/2)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
TO00 to TO03 output frequency	f_{TO}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			4	
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	
		LP (low-power main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			0.5	
		LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 3.6 V			2	
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			4	
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	
		LP (low-power main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			1	
		LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	
			1.6 V ≤ V_{DD} < 1.8 V			2	
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP6	1.6 V ≤ V_{DD} ≤ 3.6 V	1			µs
Key interrupt input low-level width	t_{KR}	KR0 to KR3	1.8 V ≤ V_{DD} ≤ 3.6 V	250			ns
			1.6 V ≤ V_{DD} < 1.8 V	1			µs
$\overline{\text{RESET}}$ low-level width	t_{RSL}			10			µs

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} < 3.6 V	f_{MCK} > 16 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 16 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 2.7 V		12/f_{MCK} and 1000		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 16		ns
		2.4 V ≤ V_{DD} < 2.7 V		t_{KCY2}/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} < 2.7 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 66	ns
			2.4 V ≤ V_{DD} < 2.7 V		2/f_{MCK} + 113	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

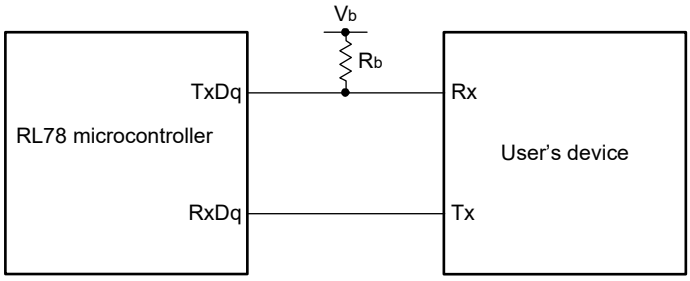
Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

Note 1. The value must also be equal to or less than f_{MCK}/4.

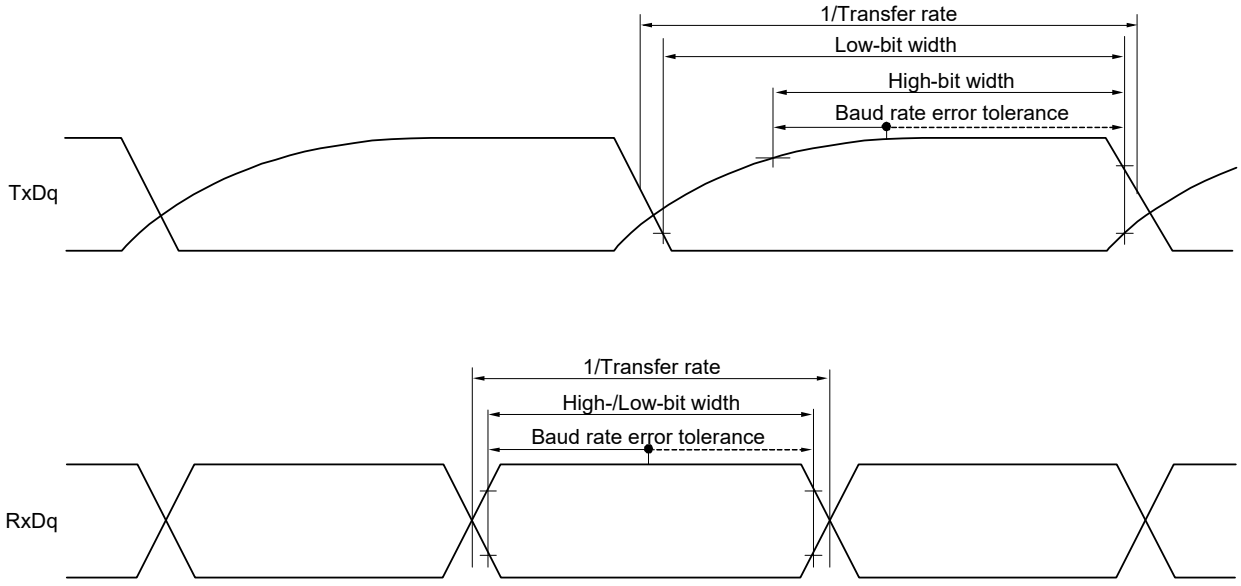
Note 2. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0), g: PIM and POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(7) Communication at different potential (2.5 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/2$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1500		1500		1500		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130		130		130	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10		10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(8) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

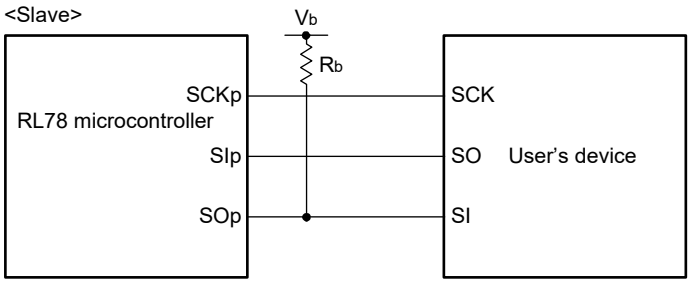
(T_A = +85 to 105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000		ns
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	2300		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 340		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 916		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 36		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the page after the next page.)

CSI mode connection diagram (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(5) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI13, ANI16 to ANI18

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tCONV	8-bit resolution	16			µs
Zero-scale error Note	EZS	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Analog input voltage	VAIN		0		V_{BGR}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(6) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI13

(T_A = +85 to +105°C, 2.4 V ≤ AV_{REFP} ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	3.375			µs
Zero-scale error Note	EZS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	LSB
Analog input voltage	VAIN			0		AV_{REFP}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(8) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target ANI16 to ANI18, internal reference voltage, temperature sensor output voltage

(T_A = +85 to +105°C, 2.4 V ≤ AVREFP ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±7.0	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	4.125			µs
Zero-scale error Note 1	EZS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
Full-scale error Note 1	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
Analog input voltage	VAIN			0		AVREFP	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 3.6 V)		VBGR Note 2			
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 3.6 V)		VTMP25 Note 2			

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AVDD pin with the same potential as the VDD pin.

2.6.3 Comparator

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref0	IVREF0 pin		0		V_{DD} - 1.4 Note	V
	Ivref1	IVREF1 pin		1.4 Note		V_{DD}	V
	Ivcmp	IVCMP0, IVCMP1 pins		-0.3		V_{DD} + 0.3	V
Output delay	td	AV_{DD} = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	µs
			Comparator high-speed mode, window mode			2.0	µs
			Comparator low-speed mode, standard mode		3.0		µs
			Comparator low-speed mode, window mode		4		µs
Operation stabilization wait time	t_{CMP}			100			µs

Note In window mode, make sure that Vref1 - Vref0 ≥ 0.2 V.

2.6.6 LVD circuit characteristics

(1) LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = -40 to +85°C, $V_{PDR} \leq AV_{DD} = V_{DD} \leq 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

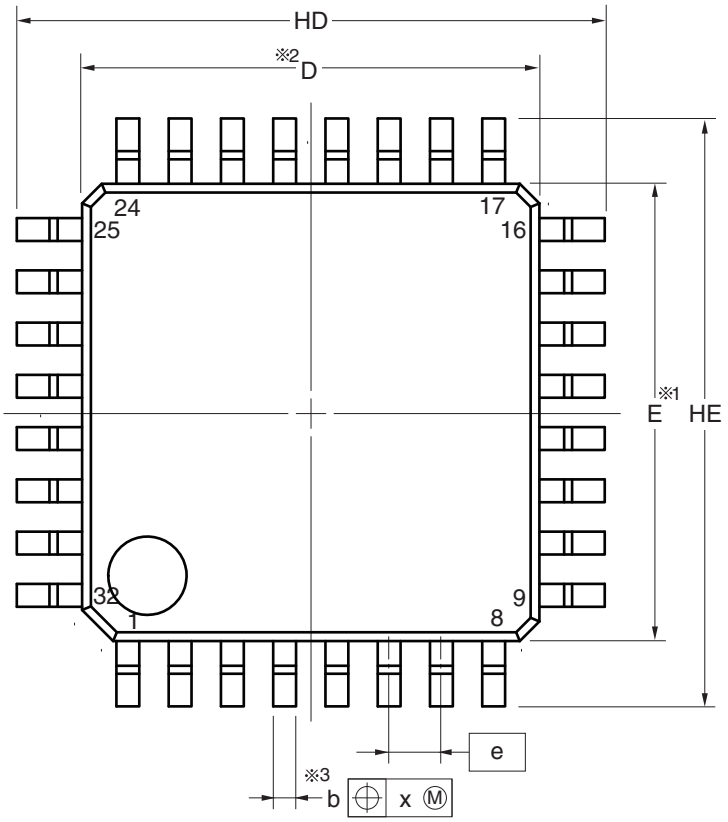
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V_{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V_{LVD10}	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		V_{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V_{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V_{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width		t_{LW}		300			µs
Detection delay time						300	µs

(T_A = +85 to +105°C, $V_{PDR} \leq AV_{DD} = V_{DD} \leq 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

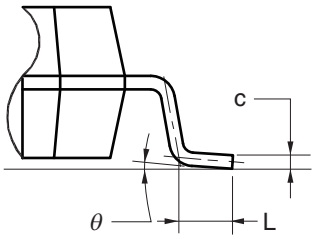
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		V_{LVD3}	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		V_{LVD4}	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		V_{LVD5}	Power supply rise time	2.71	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		V_{LVD6}	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		V_{LVD7}	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width		t_{LW}		300			µs
Detection delay time						300	µs

R5F117BAGFP, R5F117BCGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	7.00±0.10
E	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
A	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	0.37±0.05
c	0.145±0.055
L	0.50±0.20
θ	0° to 8°
e	0.80
x	0.20
y	0.10

NOTE

1.Dimensions “※1” and “※2” do not include mold flash.

2.Dimension “※3” does not include trim offset.

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.